

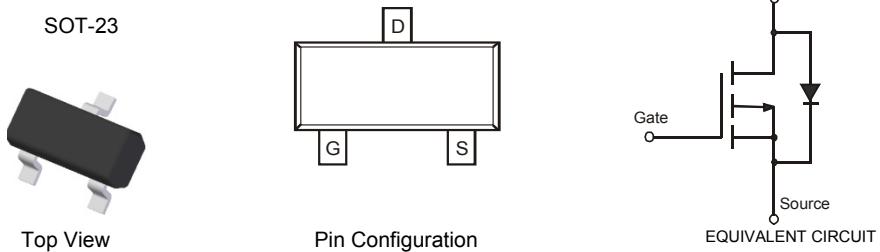
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ max	I_D $T_A = +25^\circ C$
-30V	70m Ω @ $V_{GS} = -10V$	-3.8A
	120m Ω @ $V_{GS} = -4.5V$	-3.0A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Power management functions
- Analog Switch
- Load Switch
- Boost Switch



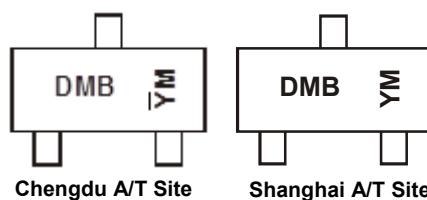
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3098L-7	SOT23	3000/Tape & Reel

Notes:

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>

Marking Information



DMB = Product Type Marking Code
YM = Date Code Marking for SAT (Shanghai Assembly/ Test site)
YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)
Y or YM = Year (ex: A = 2013)
M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015				
Code	V	W	X	Y	Z	A	B	C				
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Drain Current (Note 5) $V_{GS} = -10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	-3.8	A
		$T_A = +70^\circ\text{C}$		-2.9	
Pulsed Drain Current (Note 6)			I_{DM}	-11	A

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_D	1.08	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	115	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	-800	nA	$V_{DS} = -30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(\text{th})}$	-1.0	-1.8	-2.1	V	$V_{DS} = V_{GS}, I_D = -250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	56 98	70 120	$\text{m}\Omega$	$V_{GS} = -10\text{V}, I_D = -3.8\text{A}$ $V_{GS} = -4.5\text{V}, I_D = -3.0\text{A}$
Forward Transfer Admittance	$ Y_{fs} $	—	3.6	—	S	$V_{DS} = -5\text{V}, I_D = -2.7\text{A}$
Diode Forward Voltage (Note 6)	V_{SD}	—	—	-1.26	V	$V_{GS} = 0\text{V}, I_S = -2.7\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	336	1008	pF	$V_{DS} = -25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	70	210	pF	
Reverse Transfer Capacitance	C_{rss}	—	49	147	pF	
Gate Resistance	R_G	—	4.6	—	Ω	
SWITCHING CHARACTERISTICS (Note 8)						
Total Gate Charge	Q_g	—	4.0	8.0	nC	$V_{DS} = -15\text{V}, V_{GS} = -4.5\text{V}, I_D = -3.8\text{A}$
		—	7.8	—		$V_{DS} = -15\text{V}, V_{GS} = -10\text{V}, I_D = -3.8\text{A}$
Gate-Source Charge	Q_{gs}	—	1.0	—	ns	$V_{DS} = -15\text{V}, V_{GS} = -10\text{V}, I_D = -1\text{A}, R_G = 6.0\Omega$
Gate-Drain Charge	Q_{gd}	—	2.5	—		
Turn-On Delay Time	$t_{d(on)}$	—	6.0	12.0		
Rise Time	t_r	—	5.0	10.0		
Turn-Off Delay Time	$t_{d(off)}$	—	17.6	35.2		
Fall Time	t_f	—	9.5	19.0		

Notes: 5. Device mounted on FR-4 PCB on 2 oz., 0.5 in.² copper pads and $t \leq 5$ sec.

6. Pulse width $\leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$.

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

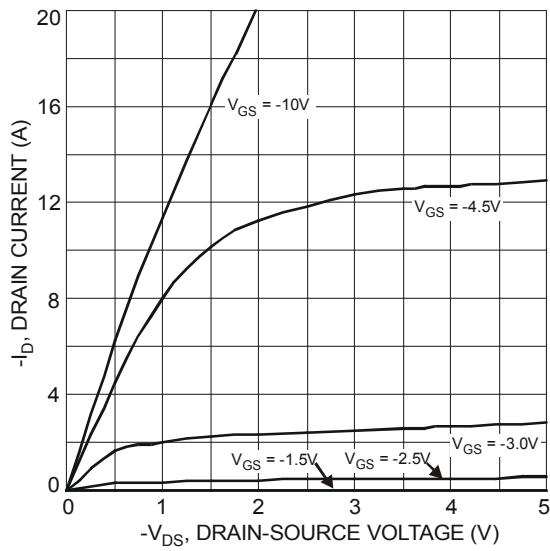


Fig. 1 Typical Output Characteristics

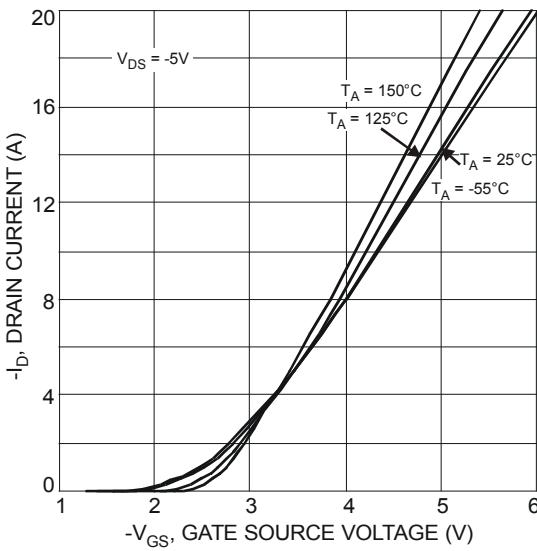


Fig. 2 Typical Transfer Characteristics

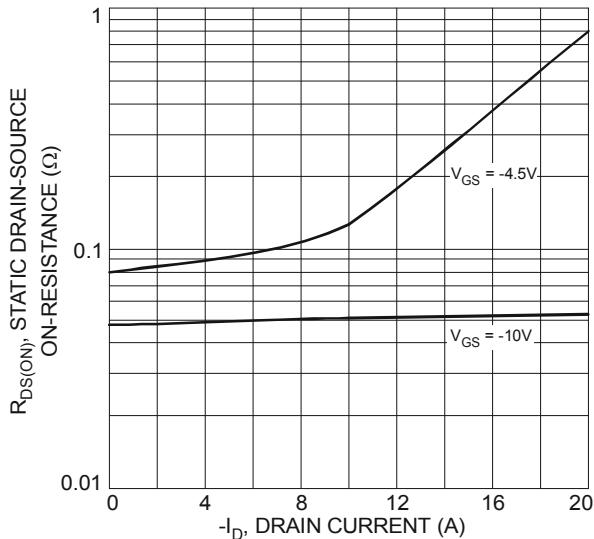


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

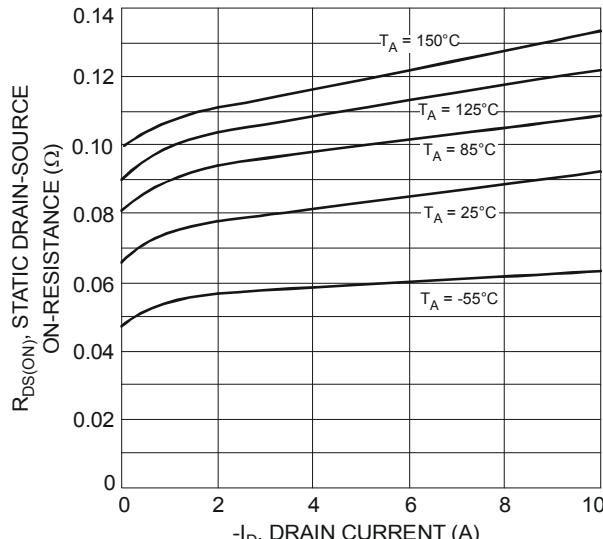


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

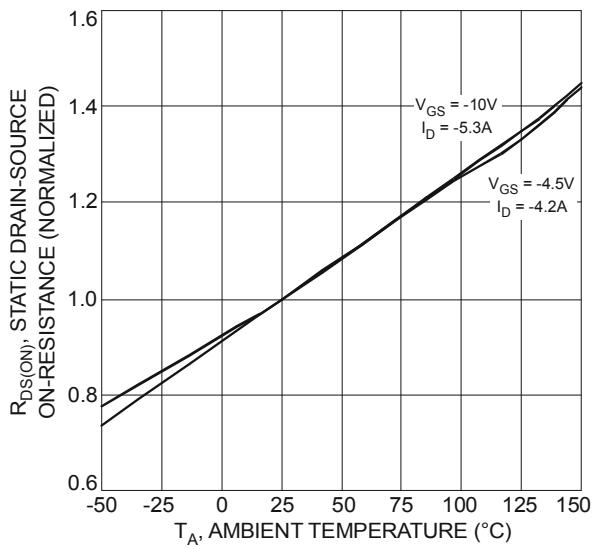


Fig. 5 On-Resistance Variation with Temperature

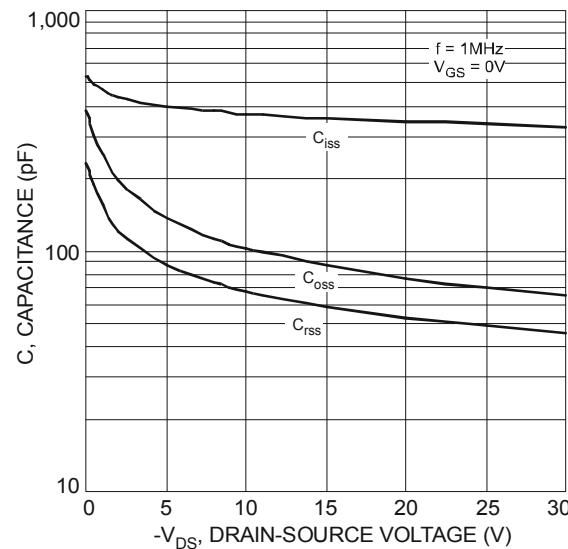


Fig. 6 Typical Capacitance

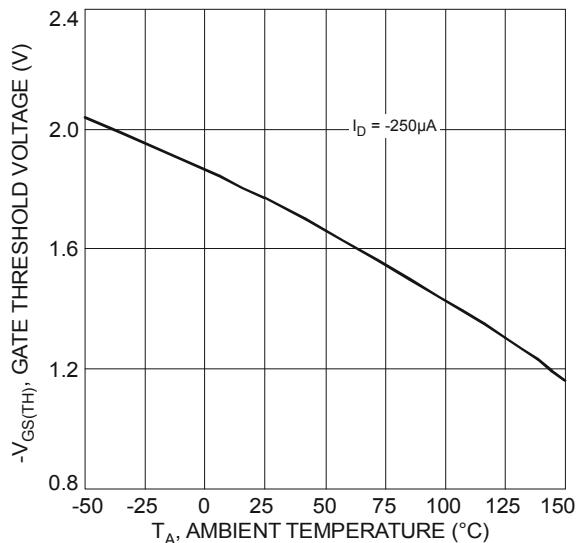


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

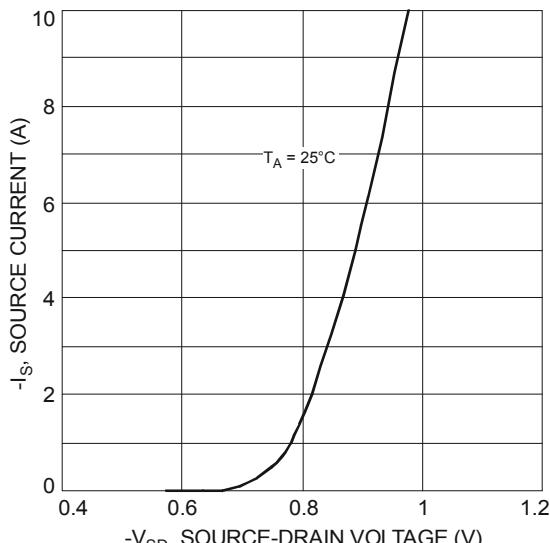


Fig. 8 Diode Forward Voltage vs. Current

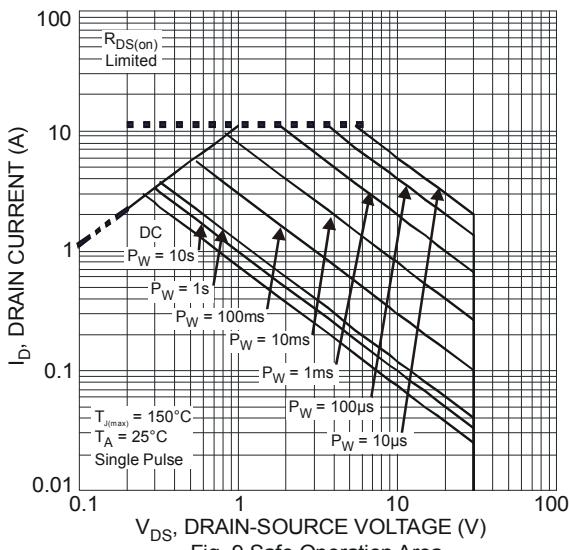
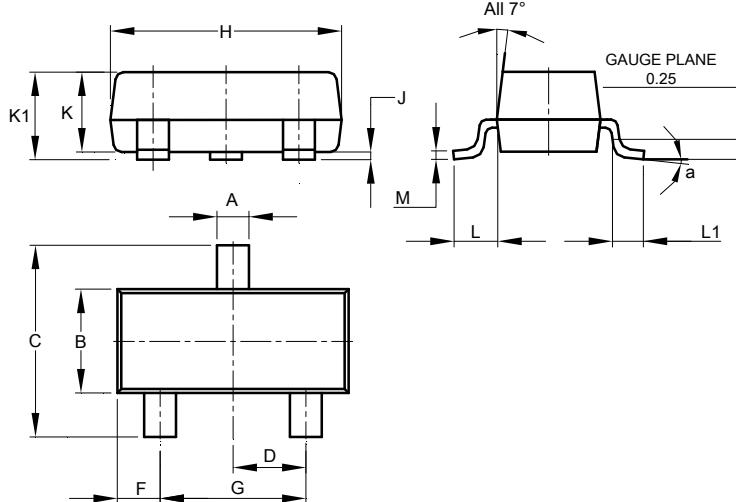


Fig. 9 Safe Operation Area

Package Outline Dimensions

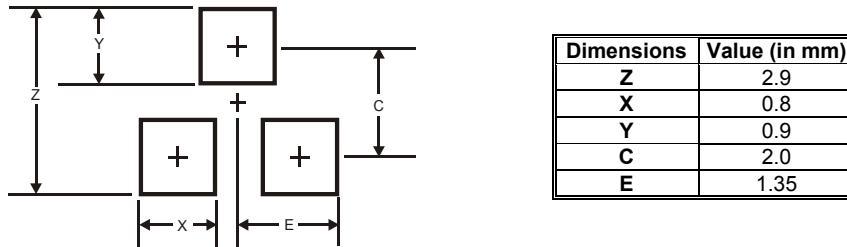
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
α	8°		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



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